

General Description

The Alpha IGBT™ line of products offers best-in-class performance in conduction and switching losses, with robust short circuit capability. They are designed for ease of paralleling, minimal gate spike under high dV/dt conditions and resistance to oscillations. The soft co-package diode is targeted for minimal losses in motor control applications.

Product Summary

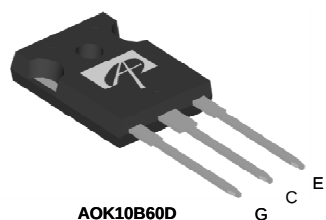
V_{CE}	600V
I_C ($T_C=100^\circ\text{C}$)	10A
$V_{CE(sat)}$ ($T_C=25^\circ\text{C}$)	1.53V

100% E_{on}/E_{off} Tested
 100% Q_{rr} Tested
 100% Short Circuit Current Tested*

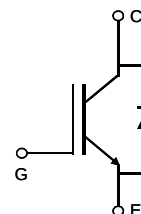


Top View

TO-247



AOK10B60D



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	AOK10B60D	Units
Collector-Emitter Voltage	V_{CE}	600	V
Gate-Emitter Voltage	V_{GE}	± 20	V
Continuous Collector Current	I_C	$T_C=25^\circ\text{C}$ 20	A
		$T_C=100^\circ\text{C}$ 10	
Pulsed Collector Current, Limited by T_{Jmax}	I_{CM}	40	A
Turn off SOA, $V_{CE} \leq 600\text{V}$, Limited by T_{Jmax}	I_{LM}	40	A
Continuous Diode Forward Current	I_F	$T_C=25^\circ\text{C}$ 20	A
		$T_C=100^\circ\text{C}$ 10	
Diode Pulsed Current, Limited by T_{Jmax}	I_{FM}	40	A
Short circuit withstanding time $V_{GE} = 15\text{V}$, $V_{CE} \leq 400\text{V}$, Delay between short circuits $\geq 1.0\text{s}$, $T_C=150^\circ\text{C}$	t_{SC}	10	μs
Power Dissipation	P_D	$T_C=25^\circ\text{C}$ 163	W
		$T_C=100^\circ\text{C}$ 82	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 175	$^\circ\text{C}$
Maximum lead temperature for soldering purpose, 1/8" from case for 5 seconds	T_L	300	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	AOK10B60D	Units
Maximum Junction-to-Ambient	$R_{\theta JA}$	40	$^\circ\text{C}/\text{W}$
Maximum IGBT Junction-to-Case	$R_{\theta JC}$	0.92	$^\circ\text{C}/\text{W}$
Maximum Diode Junction-to-Case	$R_{\theta JC}$	1.7	$^\circ\text{C}/\text{W}$

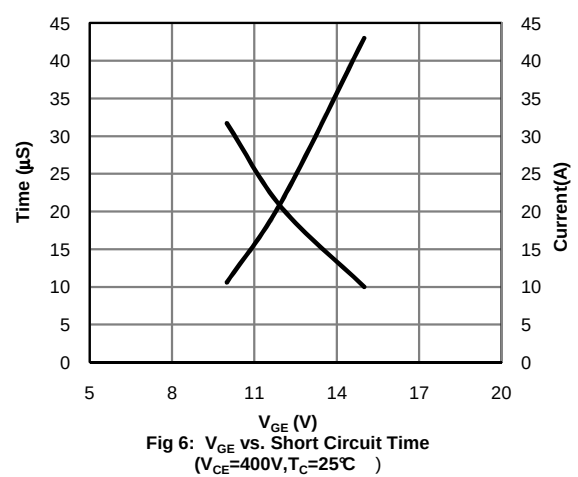
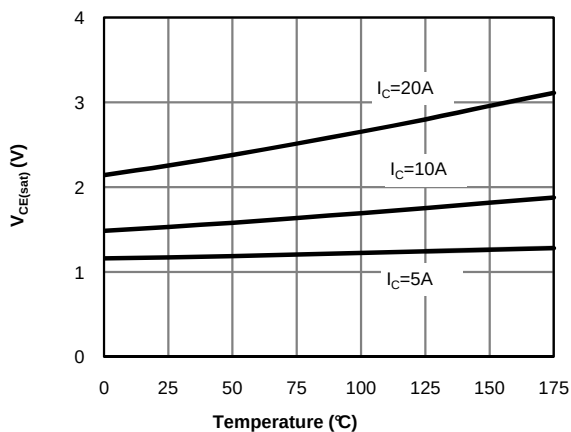
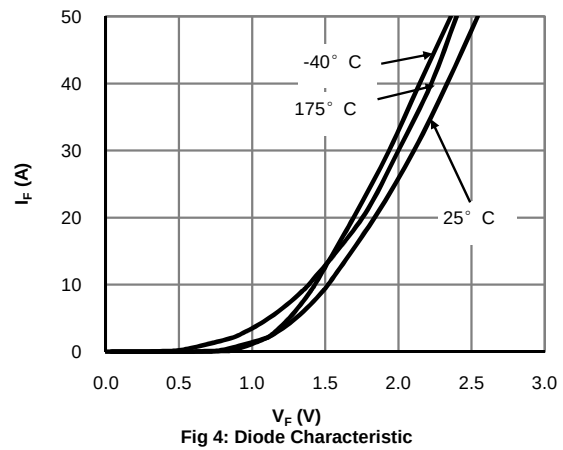
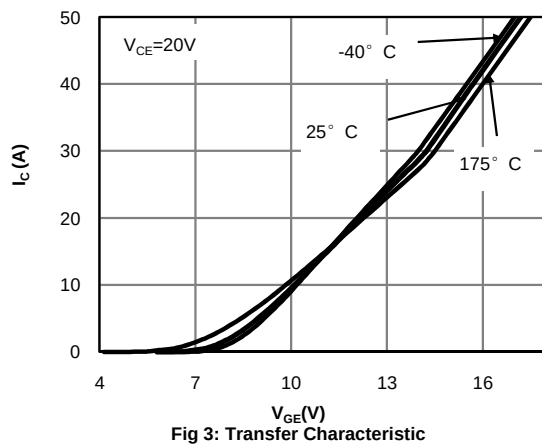
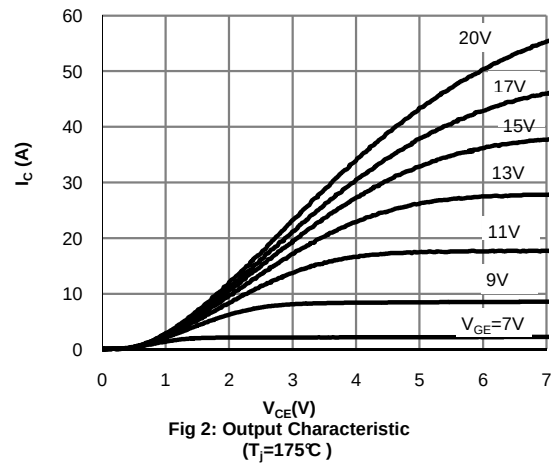
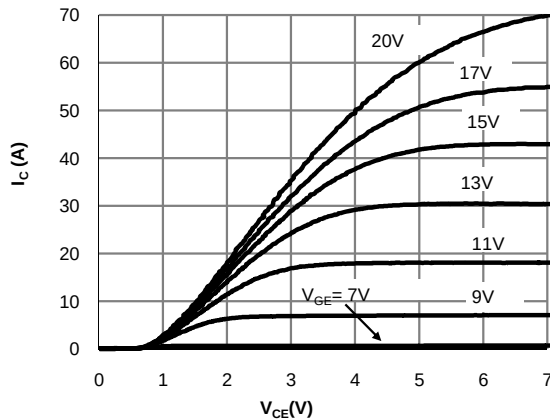
* V_{CE} equal to 50V

Electrical Characteristics (T_J=25°C unless otherwise noted)

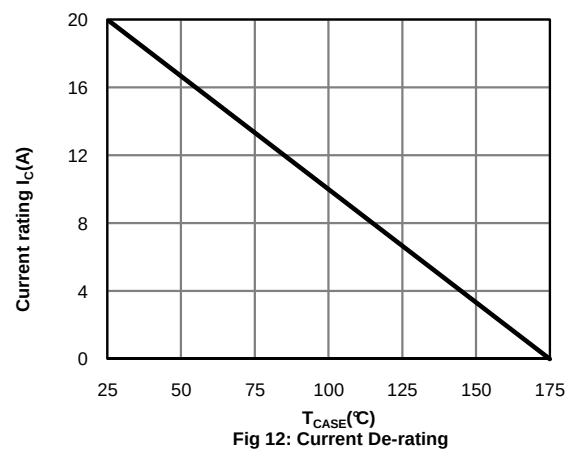
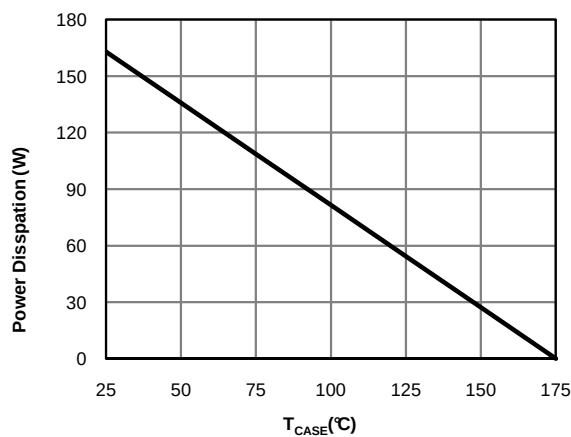
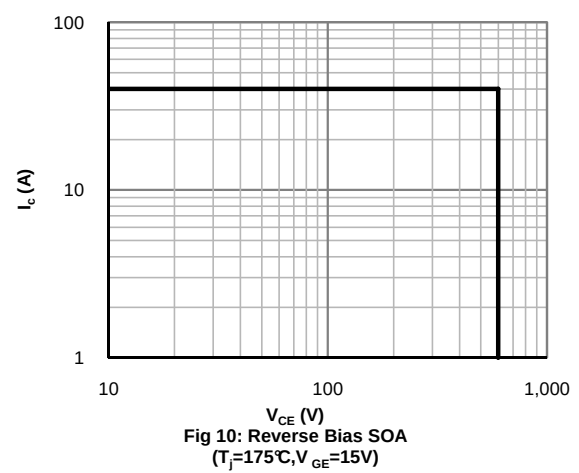
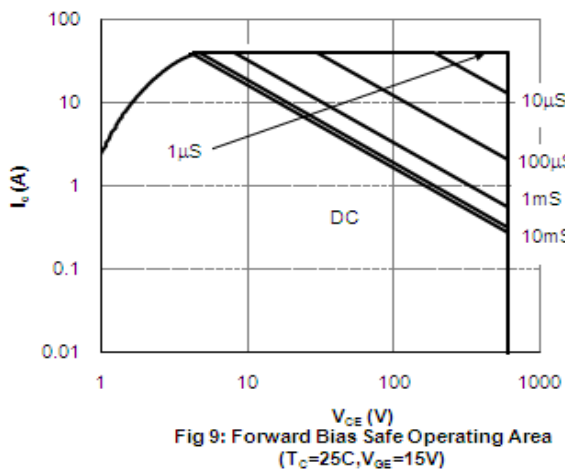
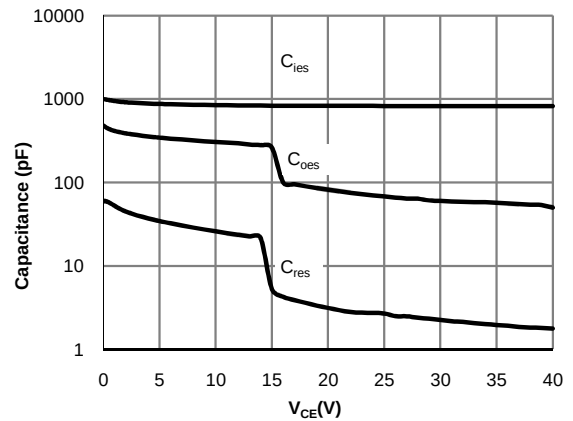
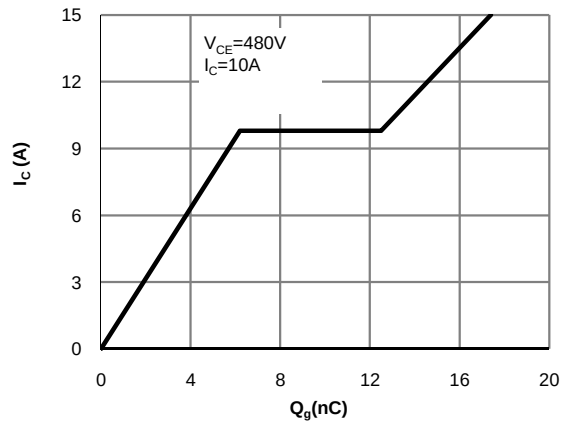
Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{CES}	Collector-Emitter Breakdown Voltage	$I_C=1mA, V_{GE}=0V, T_J=25^{\circ}C$	600	-	-	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$V_{GE}=15V, I_C=10A$	$T_J=25^{\circ}C$	-	1.53	1.8
			$T_J=125^{\circ}C$	-	1.75	-
			$T_J=175^{\circ}C$	-	1.88	-
V_F	Diode Forward Voltage	$V_{GE}=0V, I_C=10A$	$T_J=25^{\circ}C$	-	1.52	1.85
			$T_J=125^{\circ}C$	-	1.48	-
			$T_J=175^{\circ}C$	-	1.39	-
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$V_{CE}=V_{GE}, I_C=1mA$	-	5.8	-	V
I_{CES}	Zero Gate Voltage Collector Current	$V_{CE}=600V, V_{GE}=0V$	$T_J=25^{\circ}C$	-	-	10
			$T_J=125^{\circ}C$	-	-	200
			$T_J=175^{\circ}C$	-	-	2000
I_{GES}	Gate-Emitter leakage current	$V_{CE}=0V, V_{GE}=\pm 20V$	-	-	± 100	nA
g_{FS}	Forward Transconductance	$V_{CE}=20V, I_C=10A$	-	4.8	-	S
DYNAMIC PARAMETERS						
C_{ies}	Input Capacitance	$V_{GE}=0V, V_{CE}=25V, f=1MHz$	-	824	-	pF
C_{oes}	Output Capacitance		-	68	-	pF
C_{res}	Reverse Transfer Capacitance		-	2.7	-	pF
Q_g	Total Gate Charge	$V_{GE}=15V, V_{CE}=480V, I_C=10A$	-	17.4	-	nC
Q_{ge}	Gate to Emitter Charge		-	6.2	-	nC
Q_{gc}	Gate to Collector Charge		-	6.3	-	nC
$I_{C(SC)}$	Short circuit collector current, Max. 1000 short circuits, Delay between short circuits $\geq 1.0s$	$V_{GE}=15V, V_{CE}=400V, R_G=30\Omega$	-	43	-	A
R_g	Gate resistance	$V_{GE}=0V, V_{CE}=0V, f=1MHz$	-	3.2	-	Ω
SWITCHING PARAMETERS, (Load Inductive, $T_J=25^{\circ}C$)						
$t_{D(on)}$	Turn-On DelayTime	$T_J=25^{\circ}C$ $V_{GE}=15V, V_{CE}=400V, I_C=10A,$ $R_G=30\Omega,$ Parasitic Inductance=150nH	-	13	-	ns
t_r	Turn-On Rise Time		-	19	-	ns
$t_{D(off)}$	Turn-Off Delay Time		-	68	-	ns
t_f	Turn-Off Fall Time		-	10	-	ns
E_{on}	Turn-On Energy		-	0.32	-	mJ
E_{off}	Turn-Off Energy		-	0.07	-	mJ
E_{total}	Total Switching Energy		-	0.4	-	mJ
t_{rr}	Diode Reverse Recovery Time		$T_J=25^{\circ}C$	-	105	-
Q_{rr}	Diode Reverse Recovery Charge	$I_F=10A, dI/dt=200A/\mu s, V_{CE}=400V$	-	0.25	-	μC
I_{rm}	Diode Peak Reverse Recovery Current		-	5	-	A
SWITCHING PARAMETERS, (Load Inductive, $T_J=175^{\circ}C$)						
$t_{D(on)}$	Turn-On DelayTime	$T_J=175^{\circ}C$ $V_{GE}=15V, V_{CE}=400V, I_C=10A,$ $R_G=30\Omega,$ Parasitic Inductance=150nH	-	10.8	-	ns
t_r	Turn-On Rise Time		-	18	-	ns
$t_{D(off)}$	Turn-Off Delay Time		-	91	-	ns
t_f	Turn-Off Fall Time		-	8	-	ns
E_{on}	Turn-On Energy		-	0.42	-	mJ
E_{off}	Turn-Off Energy		-	0.12	-	mJ
E_{total}	Total Switching Energy		-	0.54	-	mJ
t_{rr}	Diode Reverse Recovery Time		$T_J=175^{\circ}C$	-	196	-
Q_{rr}	Diode Reverse Recovery Charge	$I_F=10A, dI/dt=200A/\mu s, V_{CE}=400V$	-	0.63	-	μC
I_{rm}	Diode Peak Reverse Recovery Current		-	6.8	-	A

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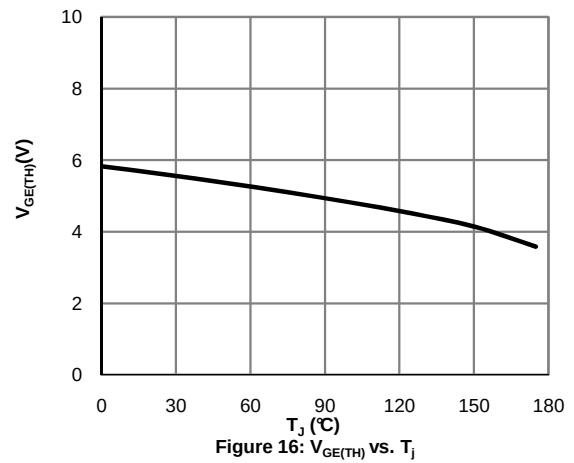
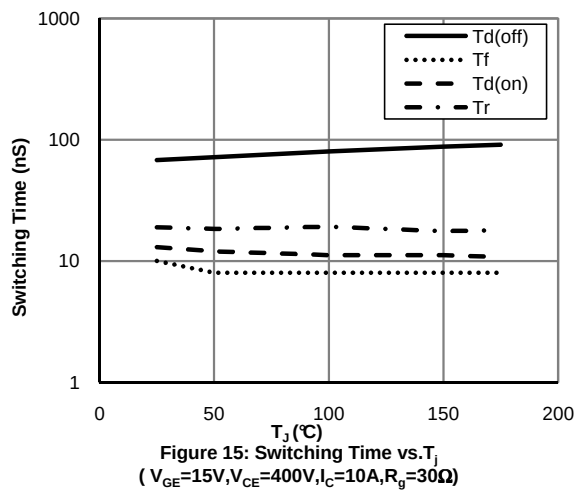
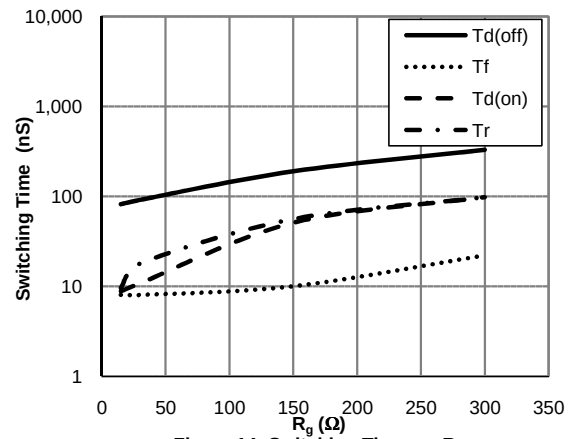
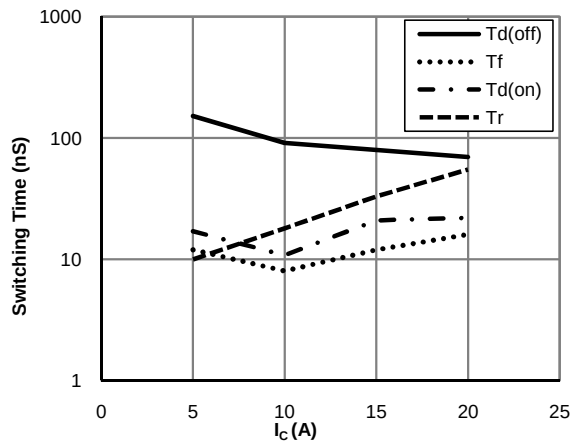
TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



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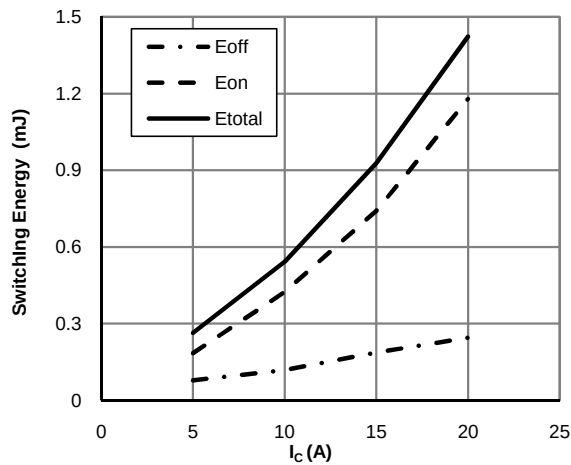


Figure 17: Switching Loss vs. I_C
($T_J=175^\circ\text{C}$, $V_{GE}=15\text{V}$, $V_{CE}=400\text{V}$, $R_g=30\Omega$)

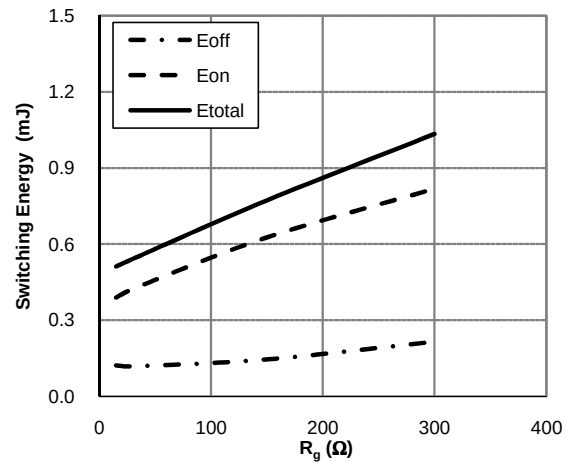


Figure 18: Switching Loss vs. R_g
($T_J=175^\circ\text{C}$, $V_{GE}=15\text{V}$, $V_{CE}=400\text{V}$, $I_C=10\text{A}$)

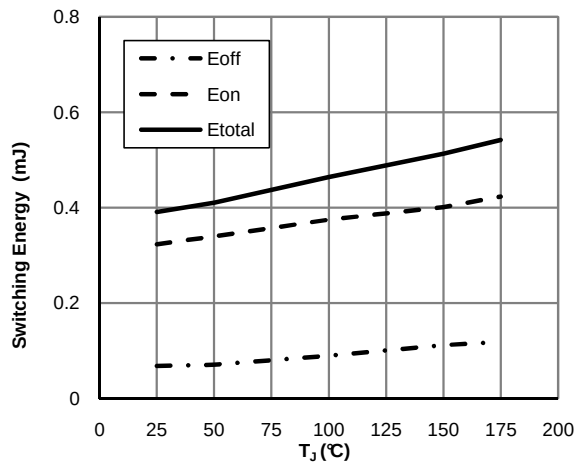


Figure 19: Switching Loss vs. T_J
($V_{GE}=15\text{V}$, $V_{CE}=400\text{V}$, $I_C=10\text{A}$, $R_g=30\Omega$)

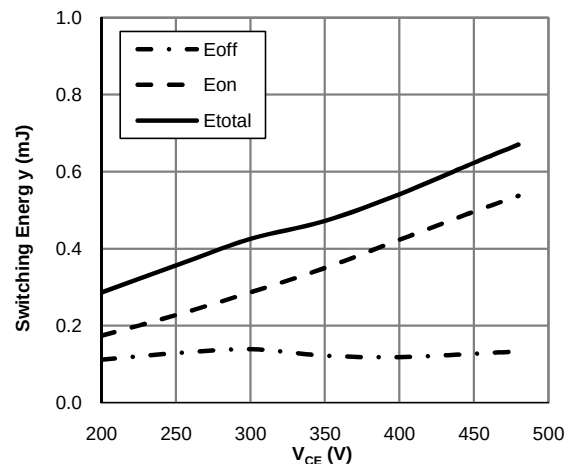


Figure 20: Switching Loss vs. V_{CE}
($T_J=175^\circ\text{C}$, $V_{GE}=15\text{V}$, $I_C=10\text{A}$, $R_g=30\Omega$)

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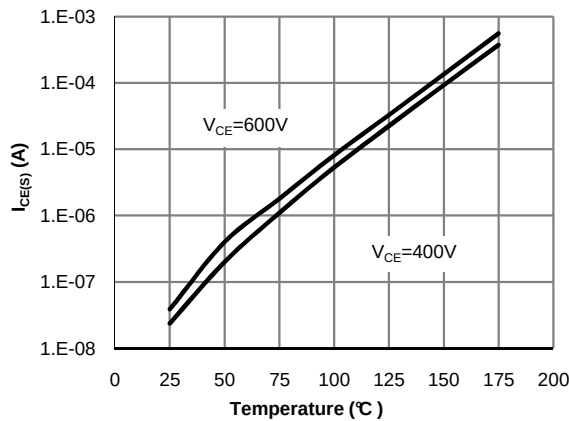


Fig 21: Diode Reverse Leakage Current vs. Junction Temperature

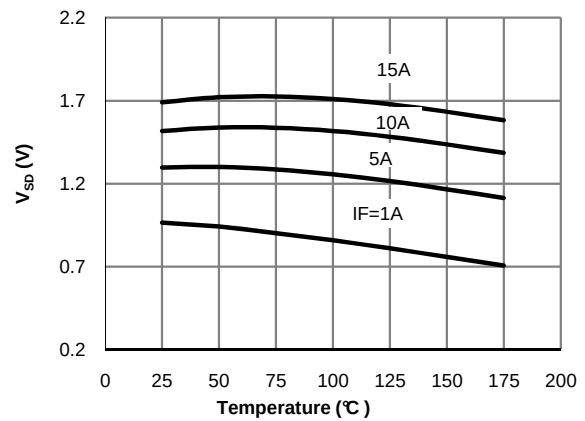


Fig 22: Diode Forward voltage vs. Junction Temperature

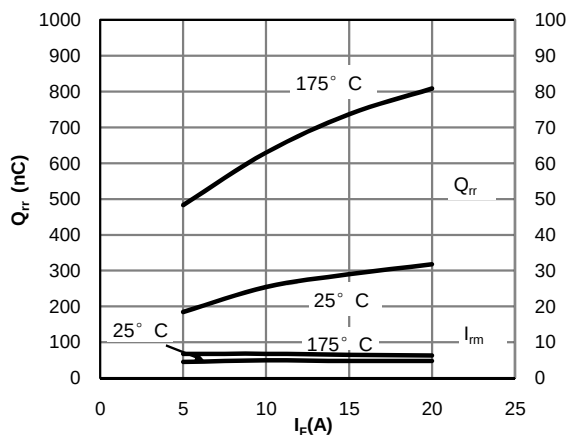


Fig 23: Diode Reverse Recovery Charge and Peak Current vs. Conduction Current
($V_{GE}=15V, V_{CE}=400V, di/dt=200A/\mu s$)

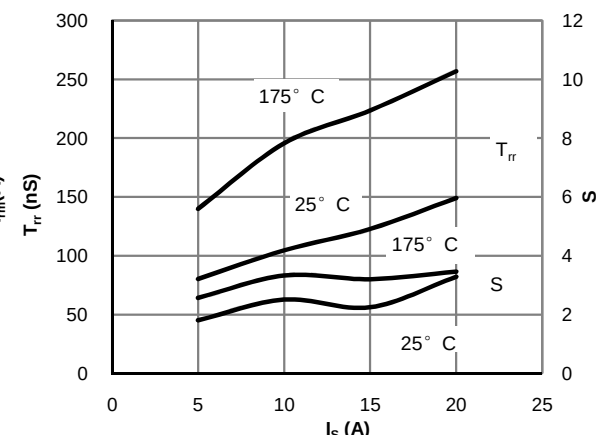


Fig 24: Diode Reverse Recovery Time and Softness Factor vs. Conduction Current
($V_{GE}=15V, V_{CE}=400V, di/dt=200A/\mu s$)

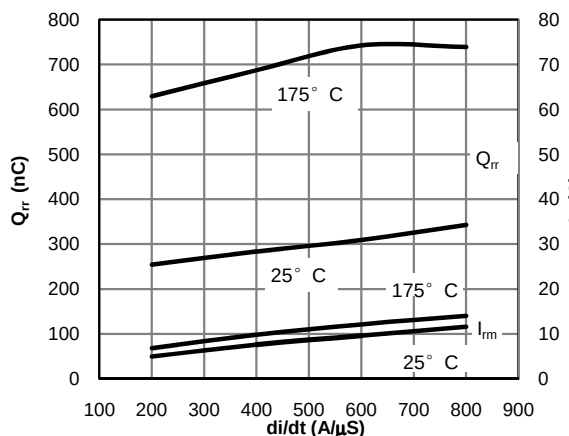


Fig 25: Diode Reverse Recovery Charge and Peak Current vs. di/dt
($V_{GE}=15V, V_{CE}=400V, I_F=10A$)

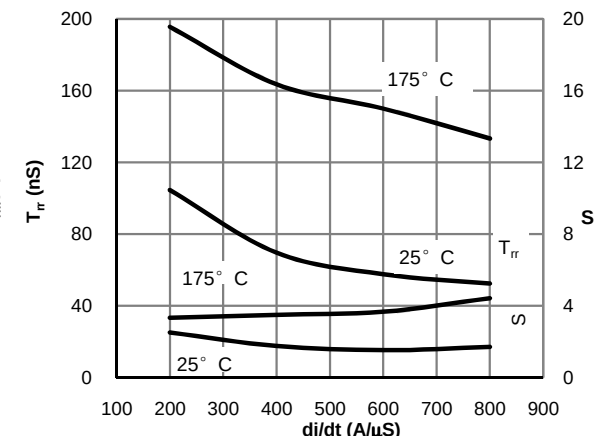


Fig 26: Diode Reverse Recovery Time and Softness Factor vs. di/dt
($V_{GE}=15V, V_{CE}=400V, I_F=10A$)

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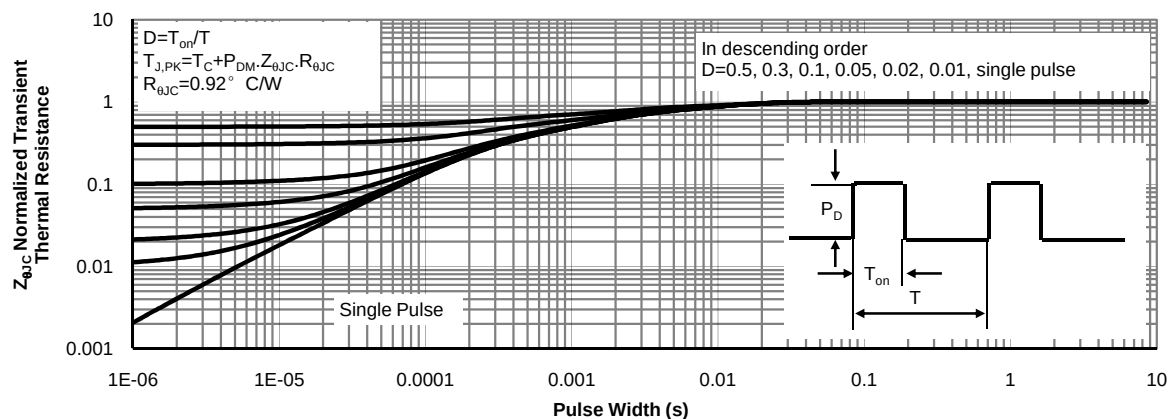


Figure 27: Normalized Maximum Transient Thermal Impedance for IGBT

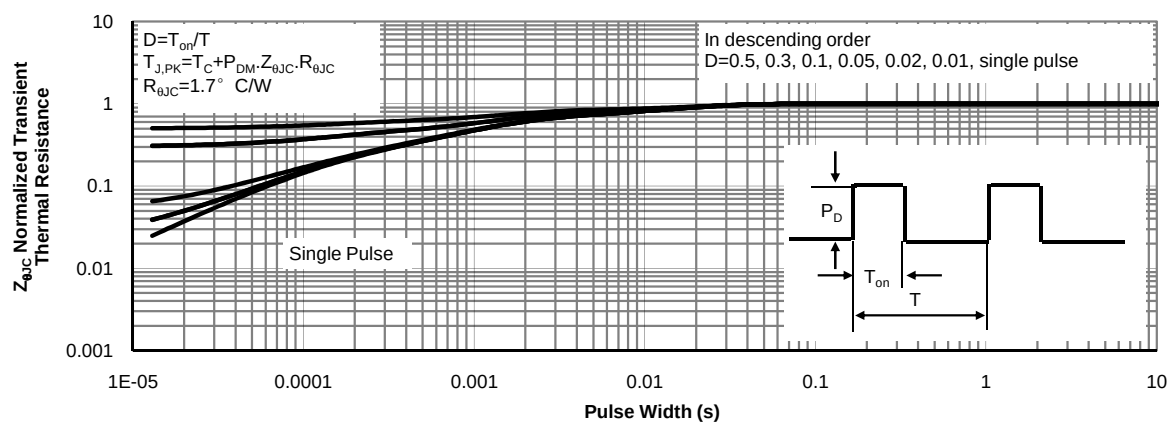
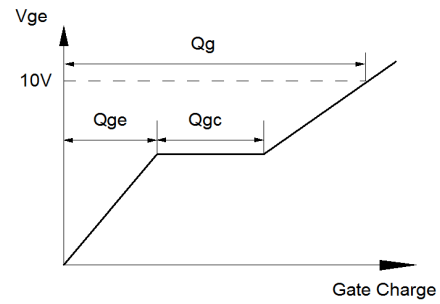
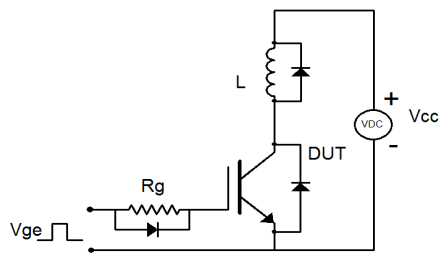
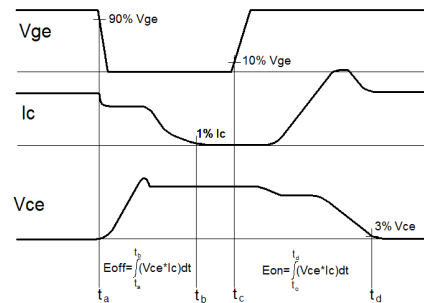
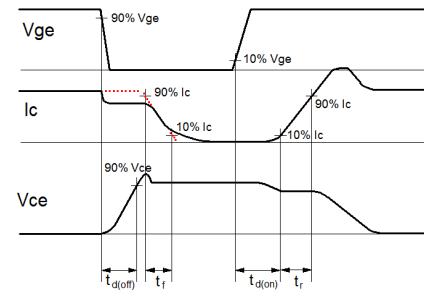
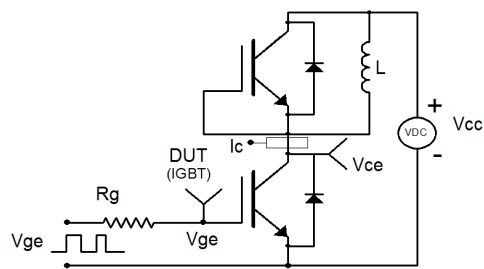


Figure 28: Normalized Maximum Transient Thermal Impedance for Diode

Gate Charge Test Circuit & Waveform



Inductive Switching Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

